Ordering number : ENN8185

SANYO Semiconductors
DATA SHEET

MCH3219 — NPN Epitaxial Planar Silicon Transistor
DC / DC Converter Applications

Applications

- Relay drivers, lamp drivers, motor drivers, flash.

Features

- Adoption of MBIT processes.
- Large current capacitance.
- Low collector-to-emitter saturation voltage.
- High-speed switching.
- Narrow h_{FE} range.
- Ultrasmall package facilitates miniaturization in end products (mounting height : 0.85mm).
- High allowable power dissipation.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		100	V
Collector-to-Emitter Voltage	V_{CES}		100	V
	V_{CEO}		50	V
Emitter-to-Base Voltage	V_{EBO}		6	V
Collector Current	I_C		1.0	A
Collector Current (Pulse)	I_{CP}		3	A
Base Current	I_B		200	mA
Collector Dissipation	P_C	Mounted on a ceramic board (600mm²×0.8m)	0.7	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=40V, I_E=0			0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=4V, I_C=0			0.1	μA
DC Current Gain	h_{FE}	V_{CE}=2V, I_C=100mA	250		400	
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=300mA		420		MHz

Marking : CP

Continued on next page.

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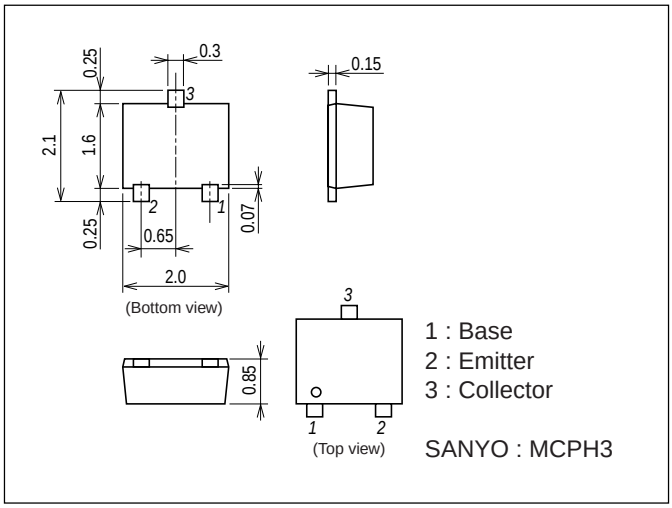
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Output Capacitance	Cob	V_{CB}=10V, f=1MHz		6		pF
Collector-to-Emitter Saturation Voltage	V_{CE}(sat)	I_C=500mA, I_B=10mA		105	160	mV
Base-to-Emitter Saturation Voltage	V_{BE}(sat)	I_C=500mA, I_B=10mA		0.81	1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=10μA, I_E=0	100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CES}$	I_C=100μA, R_{BE}=0	100			V
	$V_{(BR)CEO}$	I_C=1mA, R_{BE}=∞	50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0	6			V
Turn-ON Time	t_{on}	See specified Test Circuit.		38		ns
Storage Time	t_{stg}	See specified Test Circuit.		332		ns
Fall Time	t_f	See specified Test Circuit.		40		ns

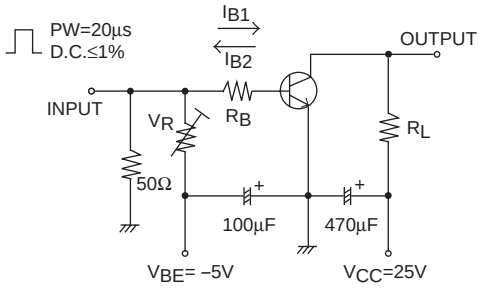
Package Dimensions

unit : mm

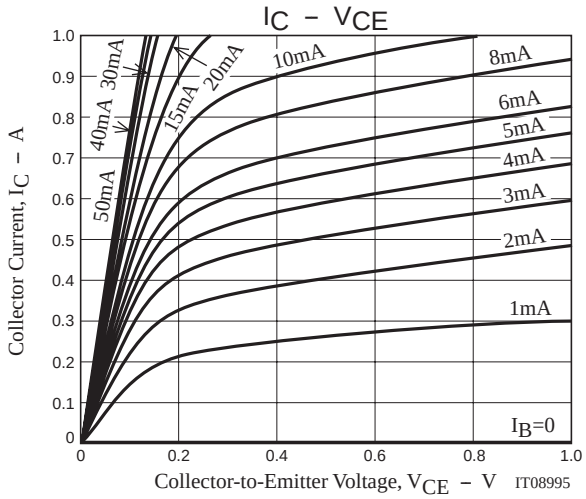
2194A

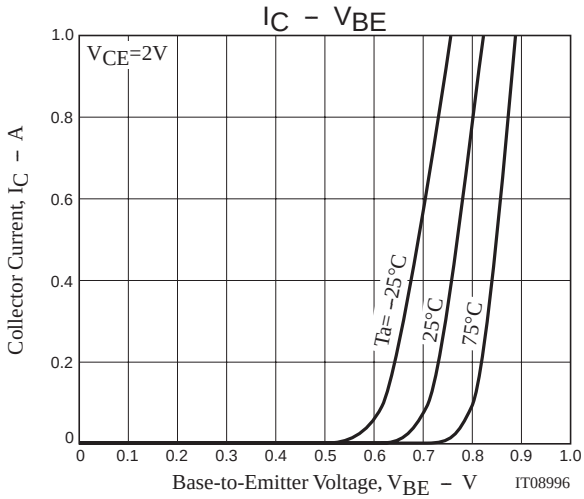


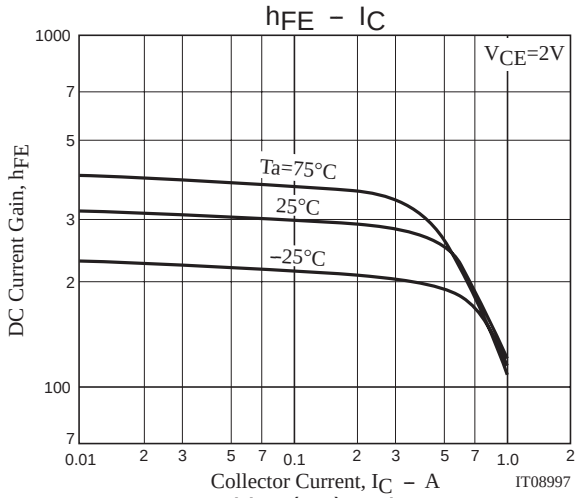
Switching Time Test Circuit

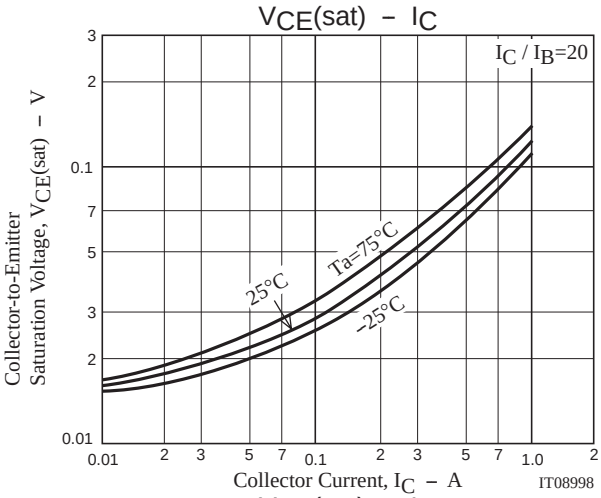


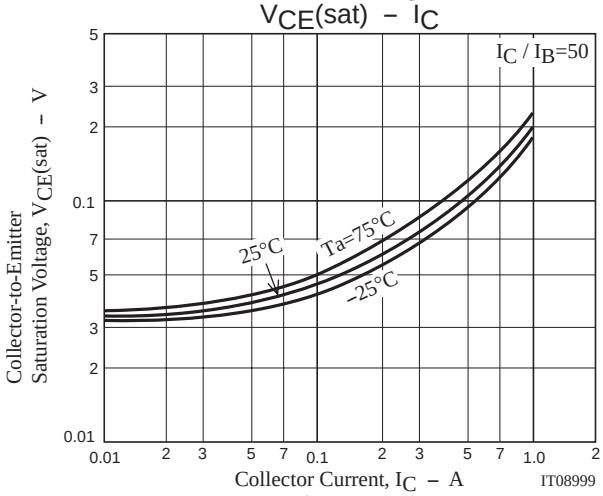
I_C=20I_{B1}= −20I_{B2}=500mA

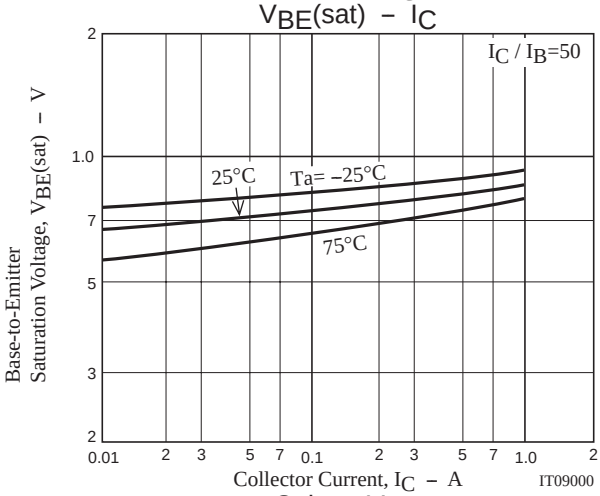


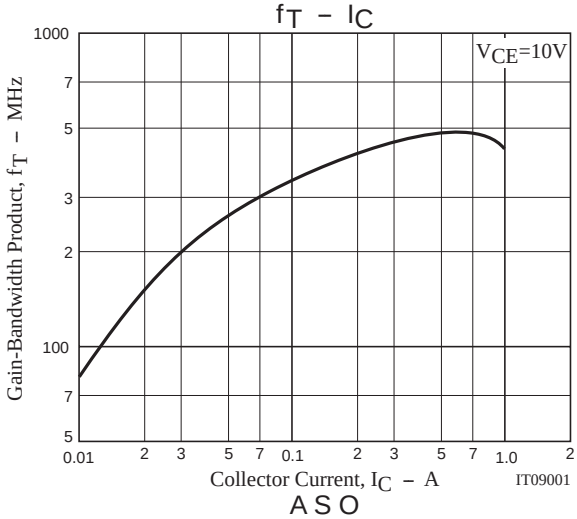


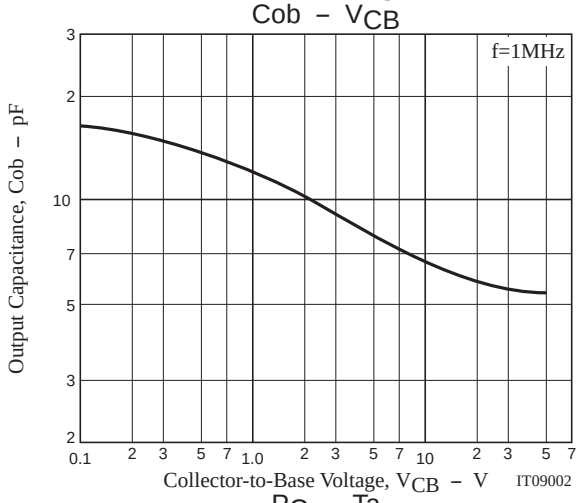

hFE – IC
VCE=2V
Ta=75°C
25°C
–25°C
DC Current Gain, hFE
Collector Current, IC – A
IT08997

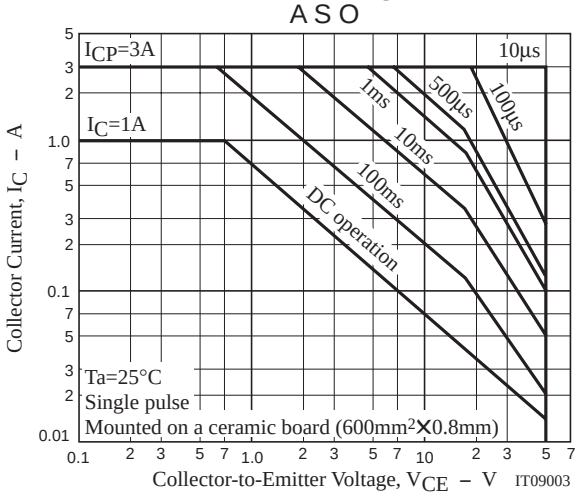

VCE(sat) – IC
IC / IB=20
Ta=75°C
25°C
–25°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – V
Collector Current, IC – A
IT08998

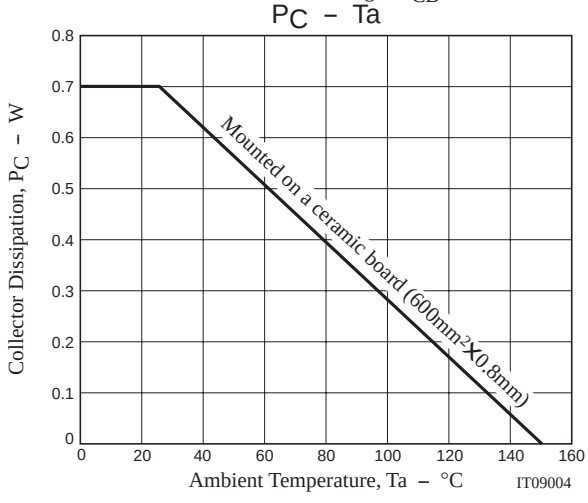

VCE(sat) – IC
IC / IB=50
Ta=75°C
25°C
–25°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – V
Collector Current, IC – A
IT08999


VBE(sat) – IC
IC / IB=50
25°C
Ta= –25°C
75°C
Base-to-Emitter Saturation Voltage, VBE(sat) – V
Collector Current, IC – A
IT09000


fT – IC
VCE=10V
Gain-Bandwidth Product, fT – MHz
Collector Current, IC – A
IT09001


Cob – VCB
f=1MHz
Output Capacitance, Cob – pF
Collector-to-Base Voltage, VCB – V
IT09002


ASO
ICP=3A
10µs
1ms
500µs
100µs
IC=1A
10ms
100ms
DC operation
Ta=25°C
Single pulse
Mounted on a ceramic board (600mm²×0.8mm)
Collector Current, IC – A
Collector-to-Emitter Voltage, VCE – V
IT09003


PC – Ta
Mounted on a ceramic board (600mm²×0.8mm)
Collector Dissipation, PC – W
Ambient Temperature, Ta – °C
IT09004